

## LPV801/LPV802 320 nA Nanopower Operational Amplifiers

### 1 Features

- Nanopower Supply Current: 320 nA/channel (typ)
- Offset Voltage: 3.5 mV (max)
- Good TcVos: 1.5  $\mu\text{V}/^\circ\text{C}$  (typ)
- Unity Gain-Bandwidth: 8 kHz
- Unity-Gain Stable
- Low Input Bias Current : 0.1pA (typ)
- Wide Supply Range: 1.6 V to 5.5 V
- Rail-to-Rail Output
- No Output Reversals
- EMI Protection
- Temperature Range:  $-40^\circ\text{C}$  to  $125^\circ\text{C}$
- Industry Standard Packages:
  - Single in 5-pin SOT-23
  - Dual in 8-pin VSSOP

### 2 Applications

- Gas Detectors such as CO and O<sub>2</sub>
- Motion Detectors Using PIR Sensors
- Ionization Smoke Alarms
- Thermostats
- Remote Sensors, IoT
- Active RFID Readers and Tags
- Portable Medical Equipment

### 3 Description

The LPV801 (single) and LPV802 (dual) comprise a family of ultra-low-power operational amplifiers for “Always ON” sensing applications in wireless and low power wired equipment. With 8kHz of bandwidth from 320nA of quiescent current, the LPV80x amplifiers minimize power consumption in equipment such as CO detectors, smoke detectors and motion detecting security systems where operational battery-life is critical.

In addition to being ultra-low-power, the LPV80x amplifiers have CMOS input stages with typically femto-amp bias currents which reduces errors commonly introduced in transimpedance amplifier (TIA) configurations with megaohm feedback resistors and high source impedance sensing applications. The LPV80x amplifiers also feature a negative-rail sensing input stage and a rail-to-rail output stage that is capable of swinging within millivolts of the rails, maintaining the widest dynamic range possible. EMI protection is designed into the LPV80x in order to reduce system sensitivity to unwanted RF signals from mobile phones, WiFi, radio transmitters and tag readers.

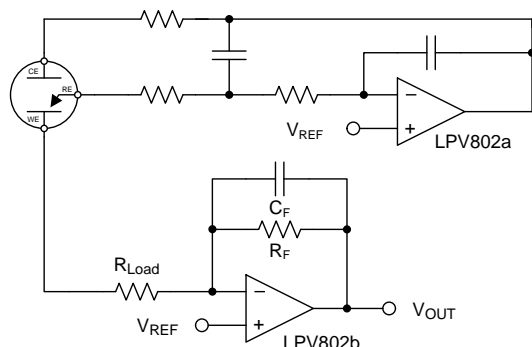
The LPV80x amplifiers operate with a total supply voltage as low as 1.6V, ensuring continuous performance in low battery situations over the extended temperature range of  $-40^\circ\text{C}$  to  $125^\circ\text{C}$ . The single and dual channel versions are available in industry standard 5-pin SOT-23 and 8-pin VSSOP packages respectively.

#### Device Information<sup>(1)</sup>

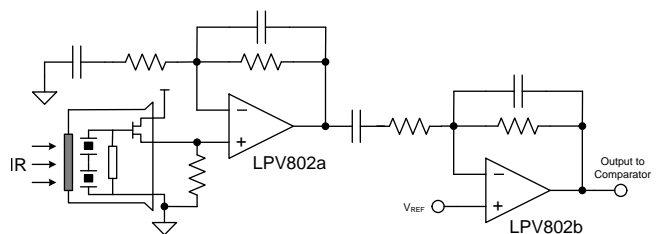
PART NUMBER	PACKAGE	BODY SIZE
LPV801	SOT-23 (5)	2.90 mm x 1.60 mm
LPV802	VSSOP (8)	3.00 mm x 3.00 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

#### Nanopower Electrochemical Sensor Amplifier



#### Nanopower PIR Motion Sensor Amplifier



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## 4 Revision History

DATE	REVISION	NOTES
June 2016	*	Initial release Product Preview

## 5 Pin Configuration and Functions



**Pin Functions: LPV801 DBV**

PIN		I/O	DESCRIPTION
NAME	NUMBER		
OUT	1	O	Output
-IN	2	I	Inverting Input
+IN	3	I	Non-Inverting Input
V-	4	P	Negative (lowest) power supply
V+	5	P	Positive (highest) power supply

**Pin Functions: LPV802 DGK**

PIN		I/O	DESCRIPTION
NAME	NUMBER		
OUT A	1	O	Channel A Output
-IN A	2	I	Channel A Inverting Input
+IN A	3	I	Channel A Non-Inverting Input
V-	4	P	Negative (lowest) power supply
+IN B	5	I	Channel B Non-Inverting Input
-IN B	6	I	Channel B Inverting Input
OUT B	7	O	Channel B Output
V+	8	P	Positive (highest) power supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

		MIN	MAX	UNIT
Supply voltage, $V_s = (V+) - (V-)$		-0.3	6	V
Input pins	Voltage <sup>(2) (3)</sup>	Common mode		(V-) - 0.3 (V+) + 0.3
		Differential		(V-) - 0.3 (V+) + 0.3
Input pins	Current	-10	10	mA
Output short current <sup>(4)</sup>		Continuous	Continuous	
Operating temperature		-40	125	°C
Storage temperature, $T_{stg}$		-65	150	°C
Junction temperature			150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Not to exceed -0.3V or +6.0V on ANY pin, referred to V-
- (3) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3 V beyond the supply rails should be current-limited to 10 mA or less.
- (4) Short-circuit to  $V_s/2$ , one amplifier per package. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

### 6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±1000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±250	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions. Pins listed as ±2000 V may actually have higher performance.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions. Pins listed as ±750 V may actually have higher performance.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Supply voltage (V+ – V-)	1.6		5.5	V
Specified temperature	-40		125	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		LPV801 DBV 5 PINS	LPV802 DGK 8 PINS	UNIT
$\theta_{JA}$	Junction-to-ambient thermal resistance	177.4	184.2	°C/W
$\theta_{Jctop}$	Junction-to-case (top) thermal resistance	133.9	75.3	
$\theta_{JB}$	Junction-to-board thermal resistance	36.3	105.5	
$\psi_{JT}$	Junction-to-top characterization parameter	23.6	13.5	
$\psi_{JB}$	Junction-to-board characterization parameter	35.7	103.9	

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

 $T_A = 25^\circ\text{C}$ ,  $V_S = 1.8\text{V}$  to  $5\text{V}$ ,  $V_{CM} = V_{OUT} = V_S/2$ , and  $R_L \geq 10\text{M}\Omega$  to  $V_S/2$ , unless otherwise noted.<sup>(1)</sup>

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFFSET VOLTAGE</b>						
$V_{OS}$	Input offset voltage	$V_S = 1.8\text{V}, 3.3\text{V}, \text{ and } 5\text{V},$ $V_{CM} = V^-$		0.55	$\pm 3.5$	mV
		$V_S = 1.8\text{V}, 3.3\text{V}, \text{ and } 5\text{V},$ $V_{CM} = (V^+) - 0.9\text{V}$		0.55	$\pm 3.5$	
$\Delta V_{OS}/\Delta T$	Input offset drift	$V_{CM} = V^-$	$T_A = -40^\circ\text{C}$ to $125^\circ\text{C}$			$\mu\text{V}/^\circ\text{C}$
PSRR	Power-supply rejection ratio	$V_S = 1.8\text{V}$ to $5\text{V},$ $V_{CM} = V^-$		1.6	60	$\mu\text{V}/\text{V}$
<b>INPUT VOLTAGE RANGE</b>						
$V_{CM}$	Common-mode voltage range	$V_S = 5\text{V}$	0		4.1	V
CMRR	Common-mode rejection ratio	$(V^-) \leq V_{CM} \leq (V^+) - 0.9\text{V}, V_S = 5\text{V}$	80	98		dB
<b>INPUT BIAS CURRENT</b>						
$I_B$	Input bias current	$V_S = 1.8\text{V}$		100		fA
$I_{OS}$	Input offset current	$V_S = 1.8\text{V}$		100		
<b>INPUT IMPEDANCE</b>						
	Differential			8		pF
	Common mode			3.8		
<b>NOISE</b>						
$E_n$	Input voltage noise	$f = 0.1\text{ Hz}$ to $10\text{ Hz}$		25		$\mu\text{Vp-p}$
$e_n$	Input voltage noise density	$f = 100\text{ Hz}$		340		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 1\text{ kHz}$		420		
<b>OPEN-LOOP GAIN</b>						
$A_{OL}$	Open-loop voltage gain	$(V^-) + 0.3\text{ V} \leq V_O \leq (V^+) - 0.3\text{ V}, R_L = 100\text{ k}\Omega$		135		dB
<b>OUTPUT</b>						
$V_{OH}$	Voltage output swing from positive rail	$V_S = 1.8\text{V}, R_L = 100\text{ k}\Omega$ to $V^+/2$	10	6		mV
$V_{OL}$	Voltage output swing from negative rail	$V_S = 1.8\text{V}, R_L = 100\text{ k}\Omega$ to $V^+/2$		4	10	
$I_{SC}$	Short-circuit current	Short to $V_S/2$		4.7		mA
$Z_O$	Open loop output impedance	$f = 1\text{ KHz}, I_O = 0\text{ A}$		94.5		k $\Omega$
<b>FREQUENCY RESPONSE</b>						
GBP	Gain-bandwidth product	$C_L = 20\text{ pF}, R_L = 10\text{ M}\Omega, V_S = 5\text{V}$		8		kHz
SR	Slew rate (10% to 90%)	$G = 1, \text{ Rising Edge}, C_L = 20\text{ pF}, V_S = 5\text{V}$		1.8		V/ms
		$G = 1, \text{ Falling Edge}, C_L = 20\text{ pF}, V_S = 5\text{V}$		1.7		
<b>POWER SUPPLY</b>						
$I_{Q-LPV801}$	Quiescent Current, Per Channel	$V_{CM} = V^-, I_O = 0, V_S = 3.3\text{ V}$		450	550	nA
$I_{Q-LPV802}$	Quiescent Current, Per Channel	$V_{CM} = V^-, I_O = 0, V_S = 3.3\text{ V}$		320	415	nA

(1) LPV801 Specifications are Preliminary until released.

## 6.6 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.

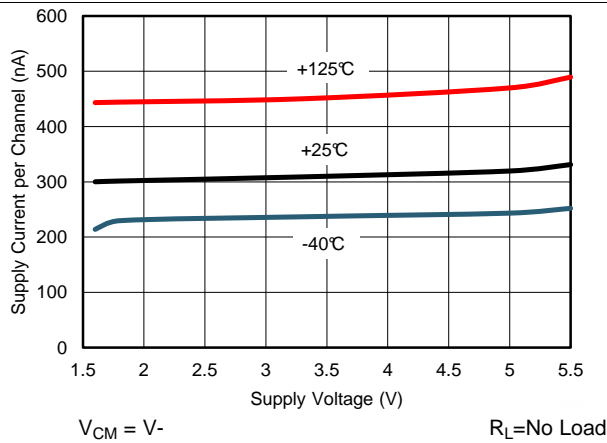


Figure 1. Supply Current vs. Supply Voltage, Low VCM

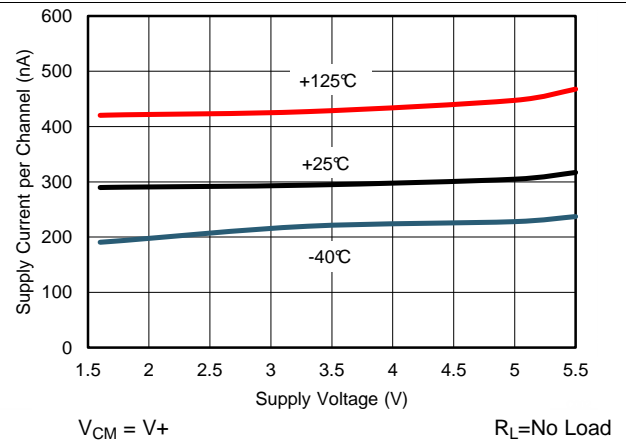


Figure 2. Supply Current vs. Supply Voltage, High VCM

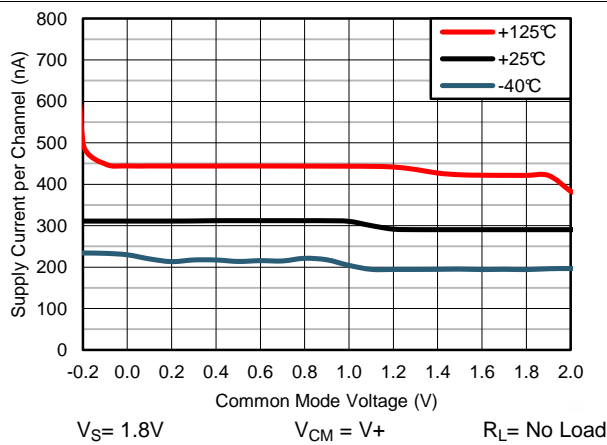


Figure 3. Supply Current vs. Common Mode Voltage, 1.8V

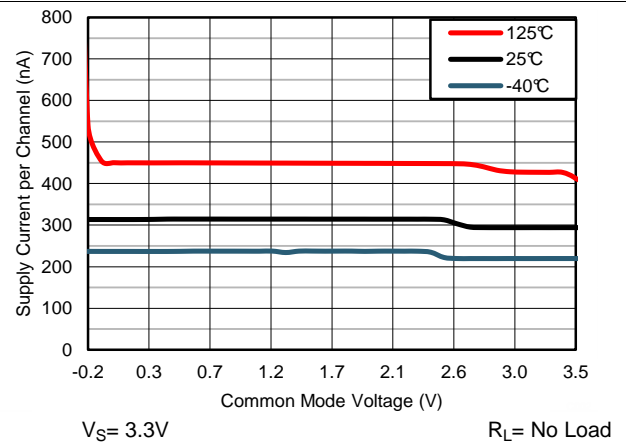


Figure 4. Supply Current vs. Common Mode Voltage, 3.3V

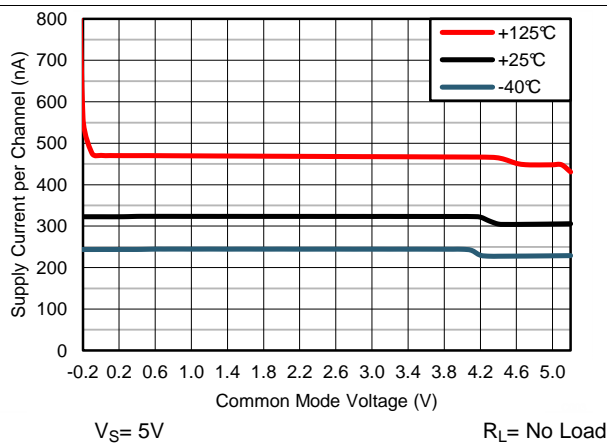


Figure 5. Supply Current vs. Common Mode Voltage, 5V

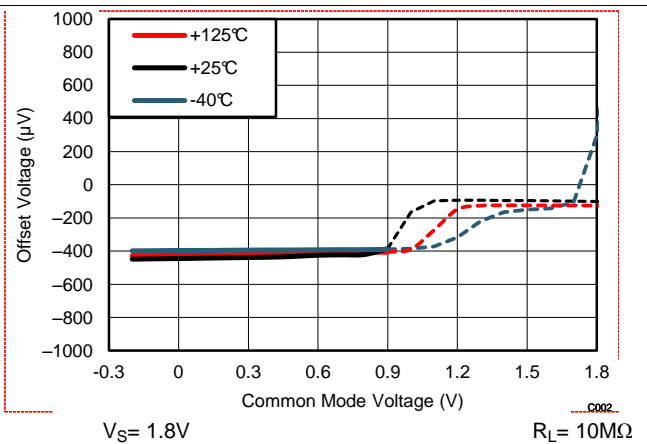


Figure 6. Typical Offset Voltage vs. Common Mode Voltage, 1.8V

Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.

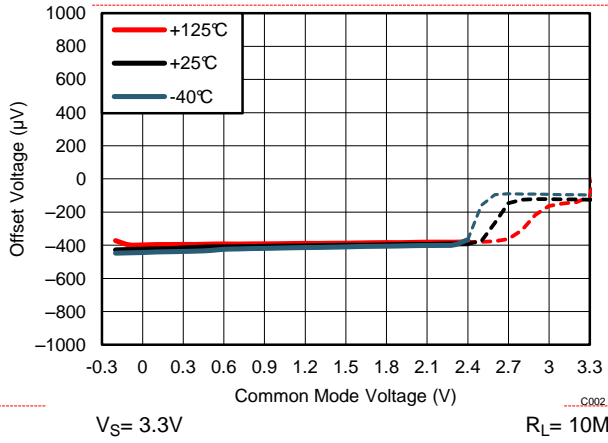


Figure 7. Typical Offset Voltage vs. Common Mode Voltage, 3.3V

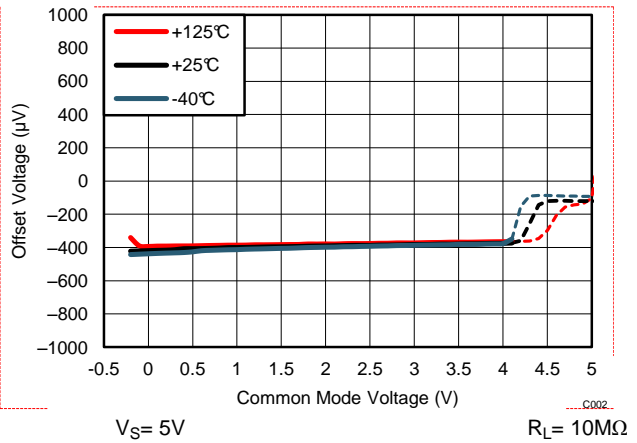


Figure 8. Typical Offset Voltage vs. Common Mode Voltage, 5V

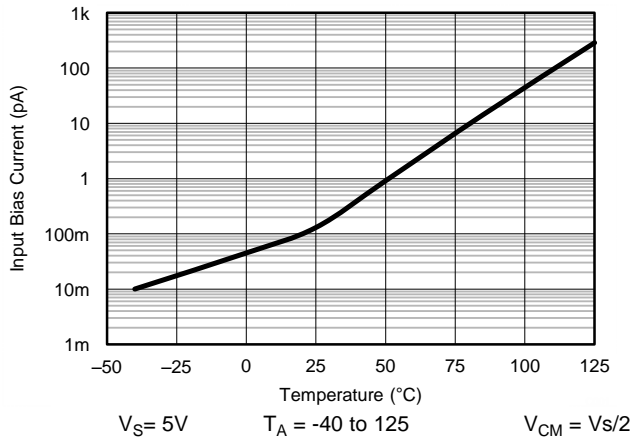


Figure 9. Input Bias Current vs. Temperature

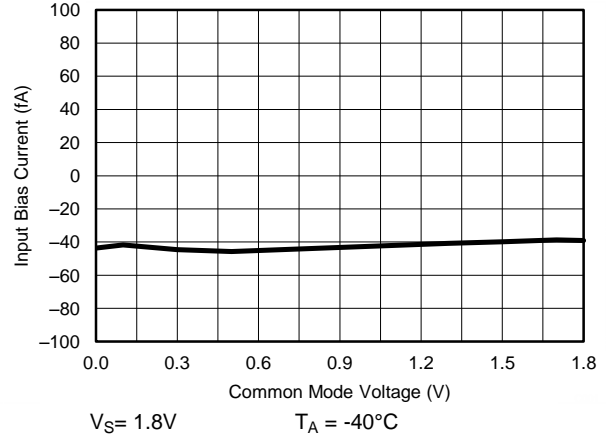


Figure 10. Input Bias Current vs. Common Mode Voltage at -40°C

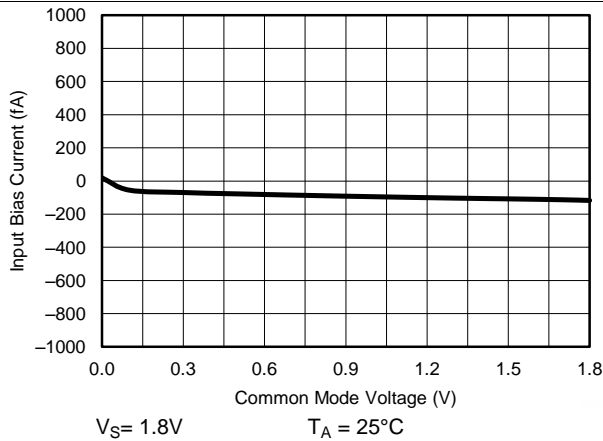


Figure 11. Input Bias Current vs. Common Mode Voltage at 25°C

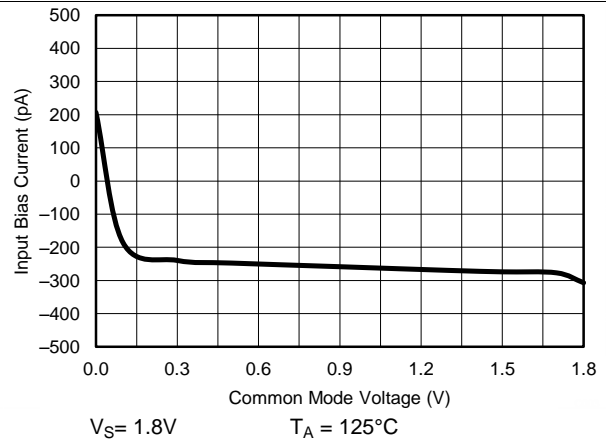
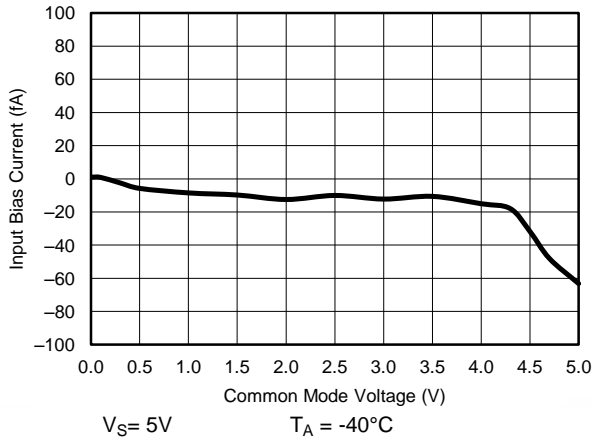


Figure 12. Input Bias Current vs. Common Mode Voltage at 125°C

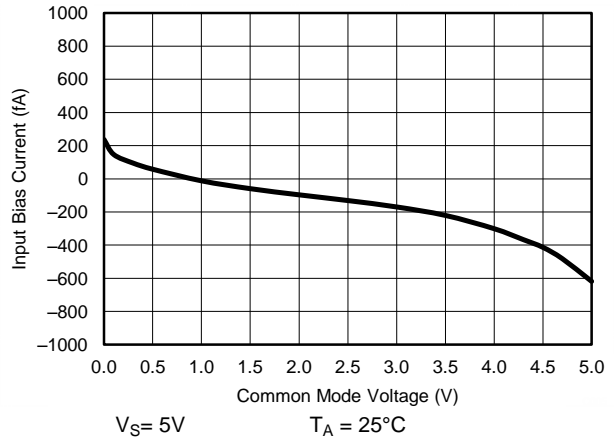
PRODUCT PREVIEW

**Typical Characteristics (continued)**

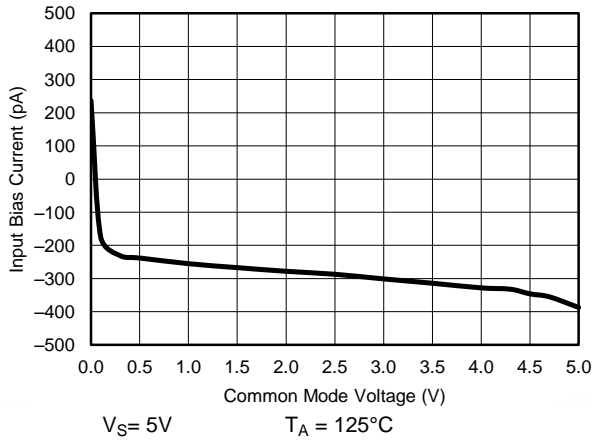
at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.



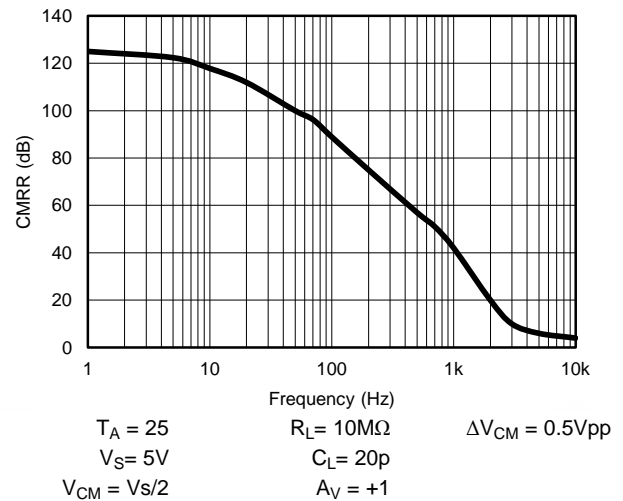
**Figure 13. Input Bias Current vs. Common Mode Voltage at -40°C**



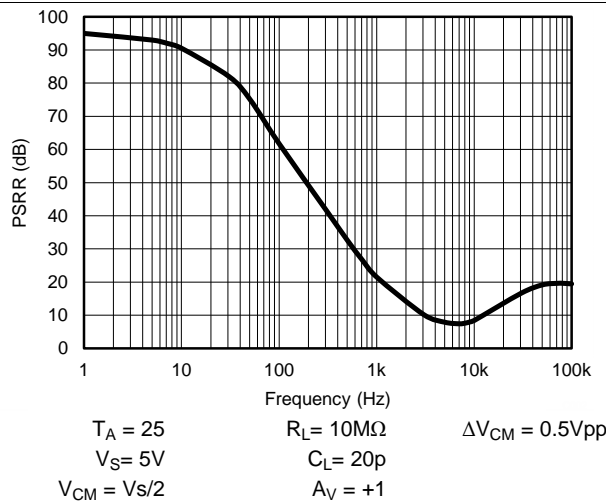
**Figure 14. Input Bias Current vs. Common Mode Voltage at 25°C**



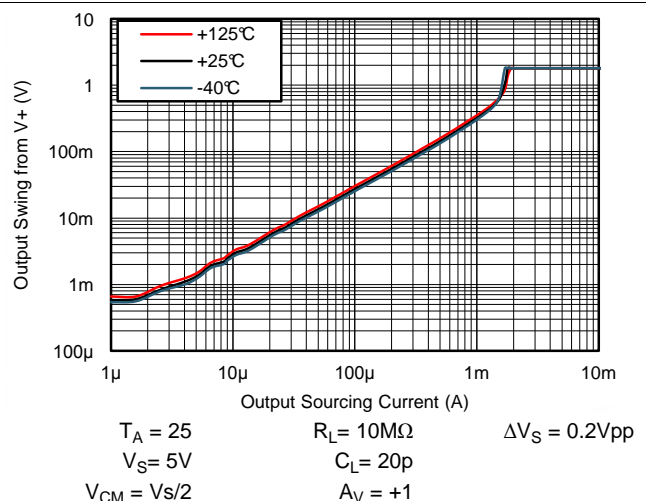
**Figure 15. Input Bias Current vs. Common Mode Voltage at 125°C**



**Figure 16. CMRR vs Frequency**



**Figure 17. ±PSRR vs Frequency**



**Figure 18. Output Swing vs. Sourcing Current, 1.8V**

PRODUCT PREVIEW

Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.

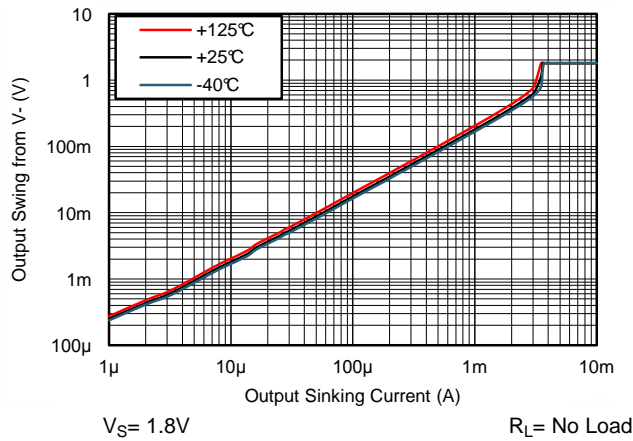


Figure 19. Output Swing vs. Sinking Current, 1.8V

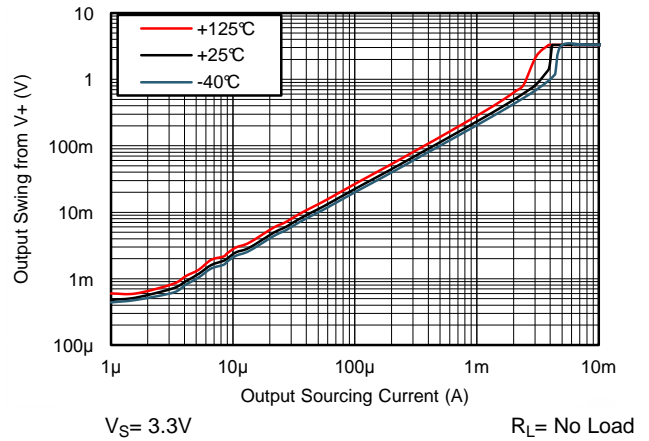


Figure 20. Output Swing vs. Sourcing Current, 3.3V

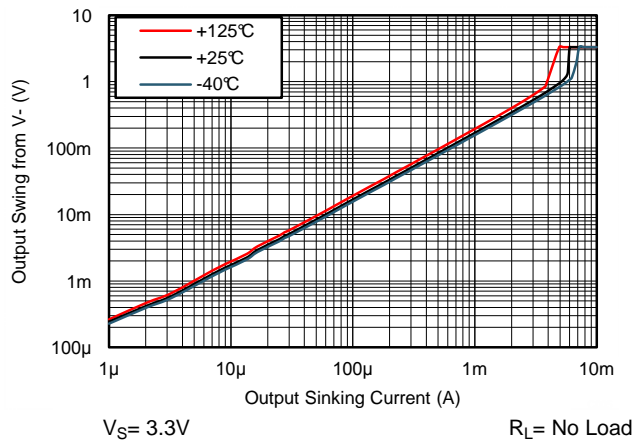


Figure 21. Output Swing vs. Sinking Current, 3.3V

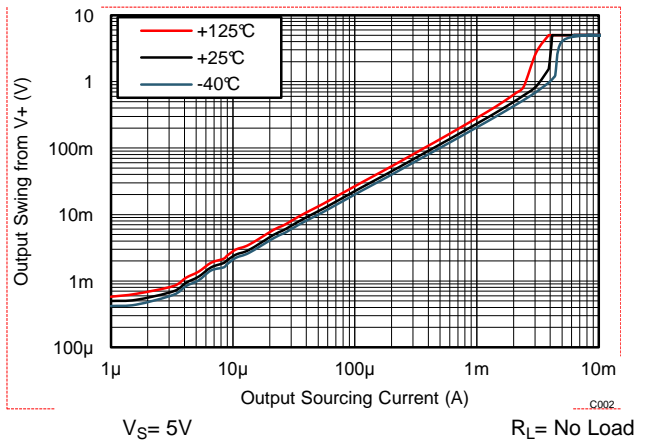


Figure 22. Output Swing vs. Sourcing Current, 5V

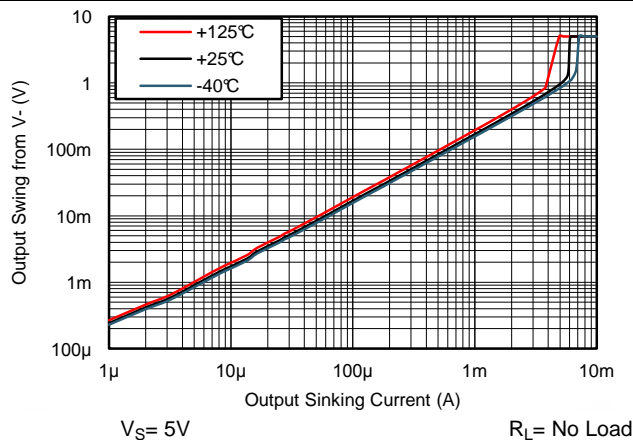
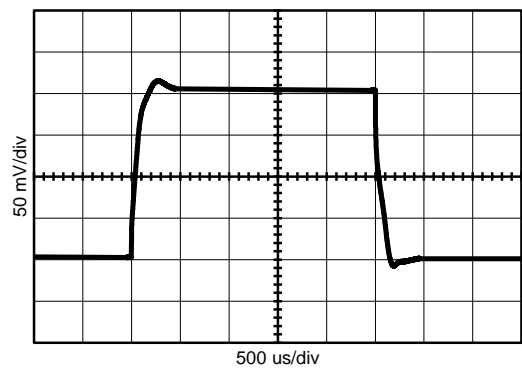


Figure 23. Output Swing vs. Sinking Current, 5V

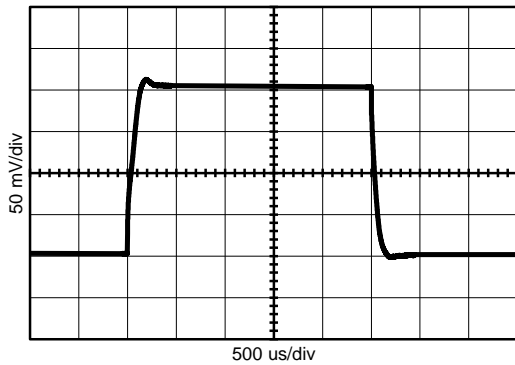


$T_A = 25$        $R_L = 10\text{M}\Omega$        $V_{out} = 200\text{mVpp}$   
 $V_S = \pm 0.9\text{V}$        $C_L = 20\text{pF}$        $A_V = +1$

Figure 24. Small Signal Pulse Response, 1.8V

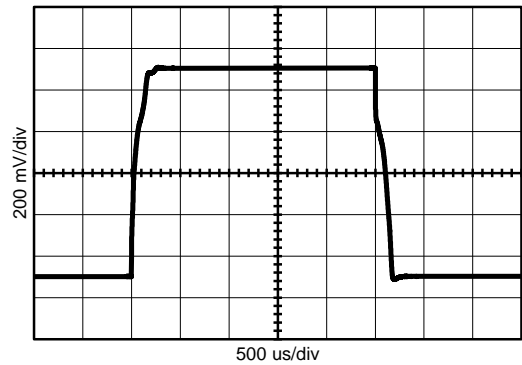
Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.



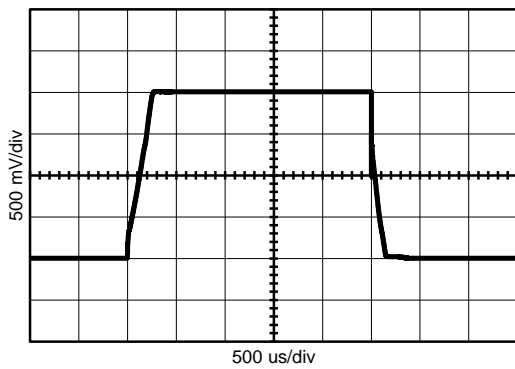
$T_A = 25$        $R_L = 10\text{M}\Omega$        $V_{out} = 200\text{mVpp}$   
 $V_S = \pm 2.5\text{V}$        $C_L = 20\text{pF}$        $A_V = +1$

Figure 25. Small Signal Pulse Response, 5V



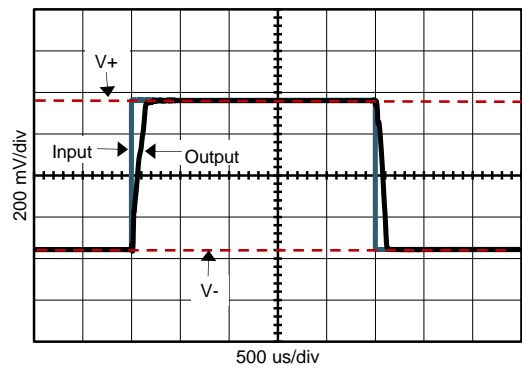
$T_A = 25$        $R_L = 10\text{M}\Omega$        $V_{out} = 1\text{Vpp}$   
 $V_S = \pm 0.9\text{V}$        $C_L = 20\text{pF}$        $A_V = +1$

Figure 26. Large Signal Pulse Response, 1.8V



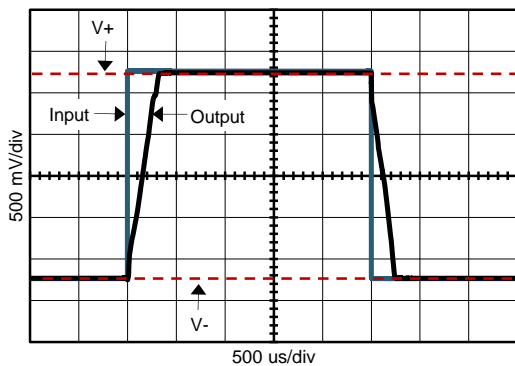
$T_A = 25$        $R_L = 10\text{M}\Omega$        $V_{out} = 2\text{Vpp}$   
 $V_S = \pm 2.5\text{V}$        $C_L = 20\text{pF}$        $A_V = +1$

Figure 27. Large Signal Pulse Response, 5V



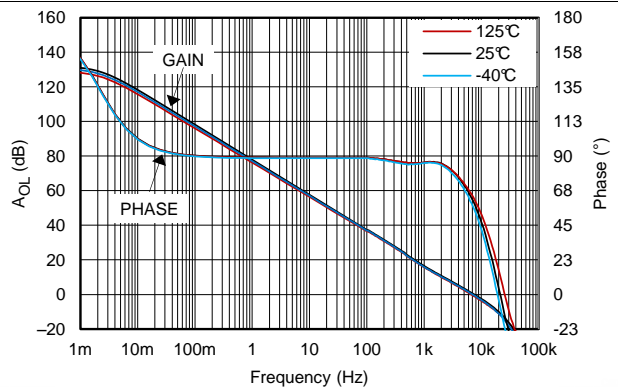
$T_A = 25$        $R_L = 10\text{M}\Omega$        $V_{out} = \pm 0.9\text{Vpp}$   
 $V_S = \pm 0.9\text{V}$        $C_L = 20\text{pF}$        $A_V = +1$

Figure 28. Rail to Rail Input Response, 1.8V



$T_A = 25$        $R_L = 10\text{M}\Omega$        $V_{out} = \pm 2.5\text{Vpp}$   
 $V_S = \pm 2.5\text{V}$        $C_L = 20\text{pF}$        $A_V = +1$

Figure 29. Rail to Rail Input Response, 5V

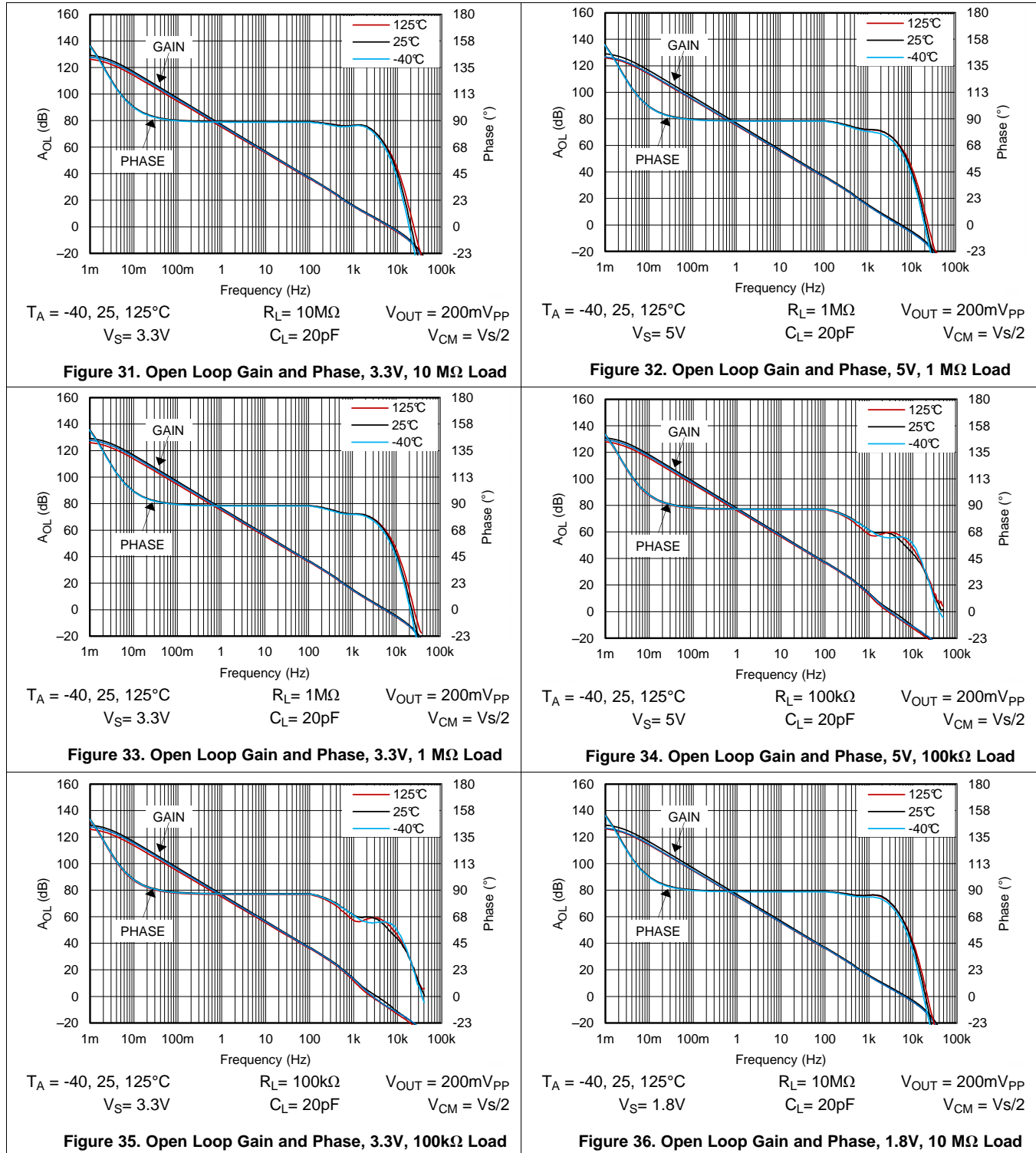


$T_A = -40, 25, 125^\circ\text{C}$        $R_L = 10\text{M}\Omega$        $V_{OUT} = 200\text{mVpp}$   
 $V_S = 5\text{V}$        $C_L = 20\text{pF}$        $V_{CM} = V_S/2$

Figure 30. Open Loop Gain and Phase, 5V, 10 MΩ Load

Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.



Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{V}$ ,  $R_L = 10\text{M}\Omega$  to  $V_S/2$ ,  $C_L = 20\text{pF}$ ,  $V_{CM} = V_S / 2\text{V}$  unless otherwise specified.

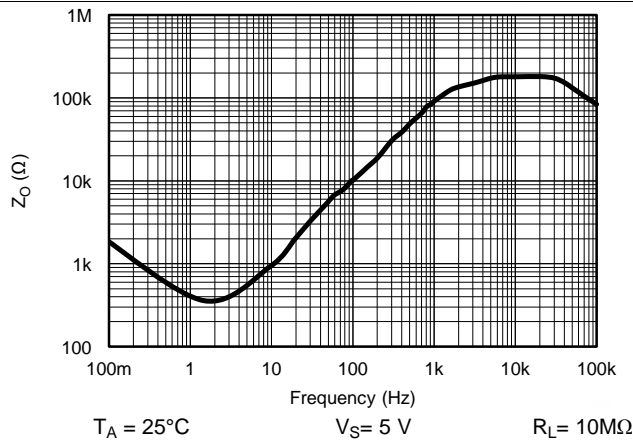


Figure 37. Open Loop Output Impedance

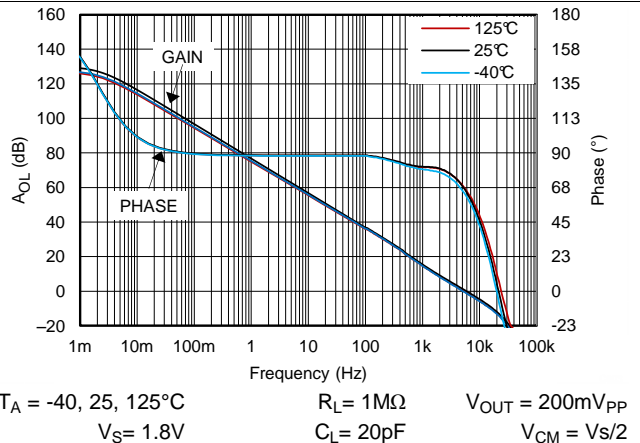


Figure 38. Open Loop Gain and Phase, 1.8V, 1 MΩ Load

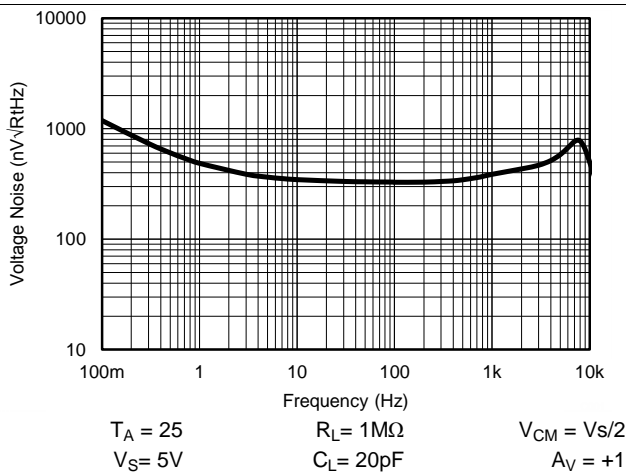


Figure 39. Voltage Noise vs Frequency

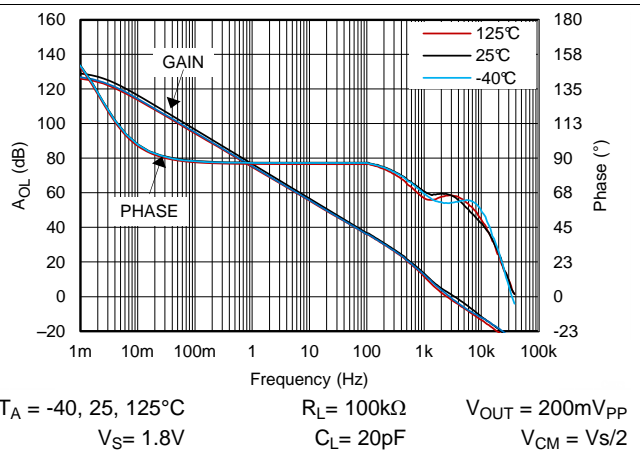


Figure 40. Open Loop Gain and Phase, 1.8V, 100kΩ Load

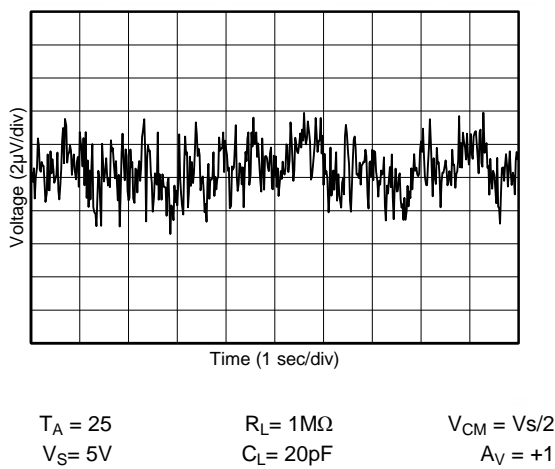


Figure 41. 0.1 to 10Hz Peak to Peak Noise

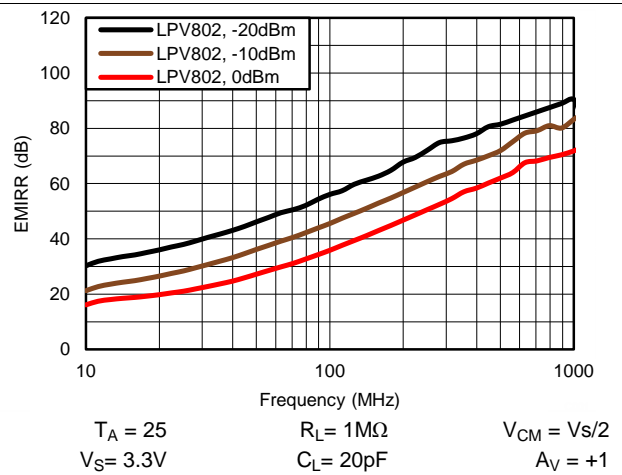


Figure 42. EMIRR Performance

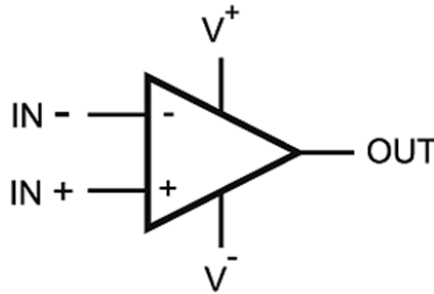
## 7 Detailed Description

### 7.1 Overview

The LPV80x is unity-gain stable and can operate on a single supply, making it highly versatile and easy to use.

Parameters that vary significantly with operating voltages or temperature are shown in the [Typical Characteristics](#) curves.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

The amplifier's differential inputs consist of a non-inverting input (+IN) and an inverting input (–IN). The amplifier amplifies only the difference in voltage between the two inputs, which is called the differential input voltage. The output voltage of the op-amp  $V_{OUT}$  is given by [Equation 1](#):

$$V_{OUT} = A_{OL} (IN^+ - IN^-)$$

where

- $A_{OL}$  is the open-loop gain of the amplifier, typically around 100 dB (100,000x, or 100,000 Volts per microvolt). (1)

### 7.4 Device Functional Modes

#### 7.4.1 Negative-Rail Sensing Input

The input common-mode voltage range of the LPV80x extends from (V-) to (V+) – 0.9 V. In this range, low offset can be expected with a minimum of 80dB CMRR. Operation of the LPV80x beyond (V+) - 0.9V is possible, however, the offset voltage is not specified. Because of this, the LPV80x is protected from output "inversions" or "reversals" as long as the input common mode voltage range stays within the input pin [Absolute Maximum Ratings](#) range.

#### 7.4.2 Rail to Rail Output Stage

The LPV80x output voltage swings 3 mV from rails at 3.3 V supply, which provides the maximum possible dynamic range at the output. This is particularly important when operating on low supply voltages.

The LPV80x Maximum Output Voltage Swing graph defines the maximum swing possible under a particular output load.

#### 7.4.3 Design Optimization for Nanopower Operation

When designing for ultralow power, choose system feedback components carefully. To minimize quiescent current consumption, select large-value feedback resistors. Any large resistors will react with stray capacitance in the circuit and the input capacitance of the operational amplifier. These parasitic RC combinations can affect the stability of the overall system. A feedback capacitor may be required to assure stability and limit overshoot or gain peaking.

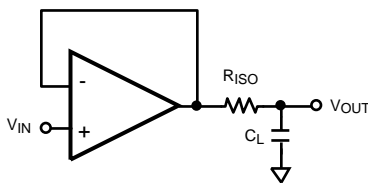
When possible, use AC coupling and AC feedback to reduce static current draw through the feedback elements. Use film or ceramic capacitors since large electrolytics may have large static leakage currents in the nanoamps.

## Device Functional Modes (continued)

### 7.4.4 Driving Capacitive Load

The LPV80x is internally compensated for stable unity gain operation, with a 8 kHz typical gain bandwidth. However, the unity gain follower is the most sensitive configuration to capacitive load. The combination of a capacitive load placed directly on the output of an amplifier along with the amplifier's output impedance creates a phase lag, which reduces the phase margin of the amplifier. If the phase margin is significantly reduced, the response will be under damped which causes peaking in the transfer and, when there is too much peaking, the op amp might start oscillating.

In order to drive heavy (>50pF) capacitive loads, an isolation resistor,  $R_{ISO}$ , should be used, as shown in Figure 43. By using this isolation resistor, the capacitive load is isolated from the amplifier's output. The larger the value of  $R_{ISO}$ , the more stable the amplifier will be. If the value of  $R_{ISO}$  is sufficiently large, the feedback loop will be stable, independent of the value of  $C_L$ . However, larger values of  $R_{ISO}$  result in reduced output swing and reduced output current drive. The recommended value for  $R_{ISO}$  is 30-50k $\Omega$ .



**Figure 43. Resistive Isolation Of Capacitive Load**

## 8 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The LPV80x is a ultra-low power operational amplifier that provides 8 kHz bandwidth with only 320nA typical quiescent current, and near precision drift specifications at a low cost. These rail-to-rail input and output amplifiers are specifically designed for battery-powered applications. The input common-mode voltage range extends to the negative supply rail and the output swings to within millivolts of the rails, maintaining a wide dynamic range.

### 8.2 Typical Application: Three Terminal CO Gas Sensor Amplifier

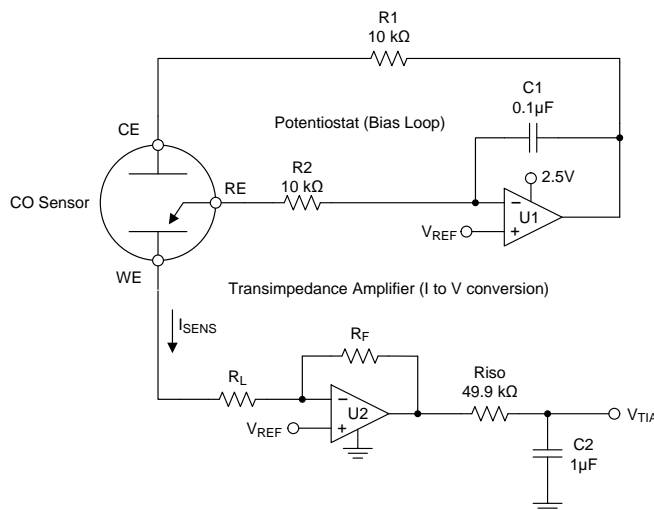


Figure 44. Three Terminal Gas Sensor Amplifier Schematic

#### 8.2.1 Design Requirements

Figure 44 shows a simple micropower potentiostat circuit for use with three terminal unbiased CO sensors, though it is applicable to many other type three terminal gas sensors or electrochemical cells.

The basic sensor has three electrodes; The Sense or Working Electrode ("WE"), Counter Electrode ("CE") and Reference Electrode ("RE"). A current flows between the CE and WE proportional to the detected concentration.

The RE monitors the potential of the internal reference point. For an unbiased sensor, the WE and RE electrodes must be maintained at the same potential by adjusting the bias on CE. Through the Potentiostat circuit formed by U1, the servo feedback action will maintain the RE pin at a potential set by  $V_{REF}$ .

R1 is to maintain stability due to the large capacitance of the sensor. C1 and R2 form the Potentiostat integrator and set the feedback time constant.

U2 forms a transimpedance amplifier ("TIA") to convert the resulting sensor current into a proportional voltage. The transimpedance gain, and resulting sensitivity, is set by  $R_F$  according to Equation 2 .

$$V_{TIA} = (-I * R_F) + V_{REF} \quad (2)$$

$R_L$  is a load resistor of which the value is normally specified by the sensor manufacturer (typically 10 ohms). The potential at WE is set by the applied  $V_{REF}$ . Riso provides capacitive isolation and, combined with C2, form the output filter and ADC reservoir capacitor to drive the ADC.

## Typical Application: Three Terminal CO Gas Sensor Amplifier (continued)

### 8.2.2 Detailed Design Procedure

For this example, we will be using a CO sensor with a sensitivity of 69nA/ppm. The supply voltage and maximum ADC input voltage is 2.5V, and the maximum concentration is 300ppm.

First the  $V_{REF}$  voltage must be determined. This voltage is a compromise between maximum headroom and resolution, as well as allowance for "footroom" for the minimum swing on the CE terminal, since the CE terminal generally goes negative in relation to the RE potential as the concentration (sensor current) increases. Bench measurements found the difference between CE and RE to be 180mV at 300ppm for this particular sensor.

To allow for negative CE swing "footroom" and voltage drop across the 10k resistor, 300mV was chosen for  $V_{REF}$ .

Therefore +300mV will be used as the minimum  $V_{ZERO}$  to add some headroom.

$$V_{ZERO} = V_{REF} = +300\text{mV}$$

where

- $V_{ZERO}$  is the zero concentration voltage
  - $V_{REF}$  is the reference voltage (300mV)
- (3)

Next we calculate the maximum sensor current at highest expected concentration:

$$I_{SENSMAX} = I_{PERPPM} * \text{ppmMAX} = 69\text{nA} * 300\text{ppm} = 20.7\mu\text{A}$$

where

- $I_{SENSMAX}$  is the maximum expected sensor current
  - $I_{PERPPM}$  is the manufacturer specified sensor current in Amps per ppm
  - ppmMAX is the maximum required ppm reading
- (4)

Now find the available output swing range above the reference voltage available for the measurement:

$$V_{SWING} = V_{OUTMAX} - V_{ZERO} = 2.5\text{V} - 0.3\text{V} = 2.2\text{V}$$

where

- $V_{SWING}$  is the expected change in output voltage
  - $V_{OUTMAX}$  is the maximum amplifier output swing (usually near V+)
- (5)

Now we calculate the transimpedance resistor ( $R_F$ ) value using the maximum swing and the maximum sensor current:

$$R_F = V_{SWING} / I_{SENSMAX} = 2.2\text{V} / 20.7\mu\text{A} = 106.28 \text{ k}\Omega \text{ (we will use } 110 \text{ k}\Omega \text{ for a common value)}$$
(6)

Typical Application: Three Terminal CO Gas Sensor Amplifier (continued)

8.2.3 Application Curve

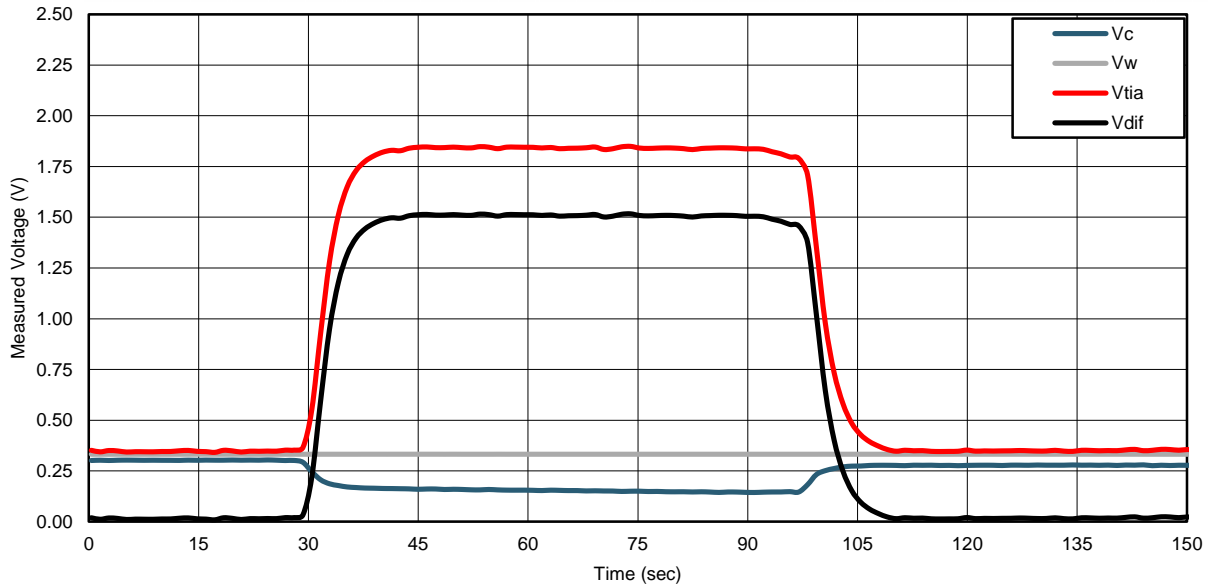


Figure 45. Monitored Voltages when exposed to 200ppm CO

Figure 45 shows the resulting circuit voltages when the sensor was exposed to 200ppm step of carbon monoxide gas.  $V_C$  is the monitored CE pin voltage and clearly shows the expected CE voltage dropping below the WE voltage,  $V_W$ , as the concentration increases.

$V_{TIA}$  is the output of the transimpedance amplifier U2.  $V_{DIFF}$  is the calculated difference between  $V_{REF}$  and  $V_{TIA}$ , which will be used for the ppm calculation.

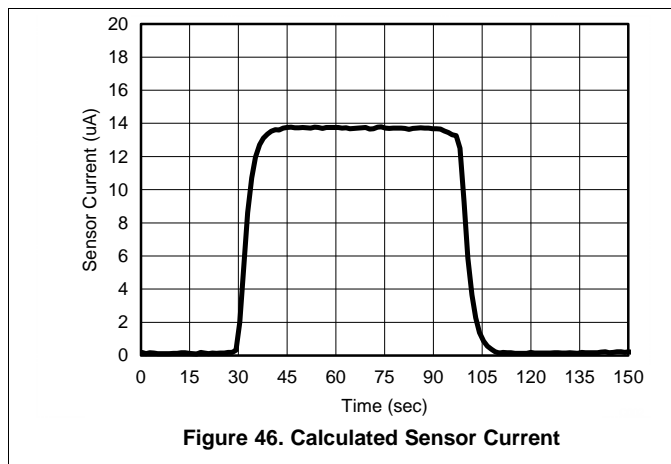


Figure 46. Calculated Sensor Current

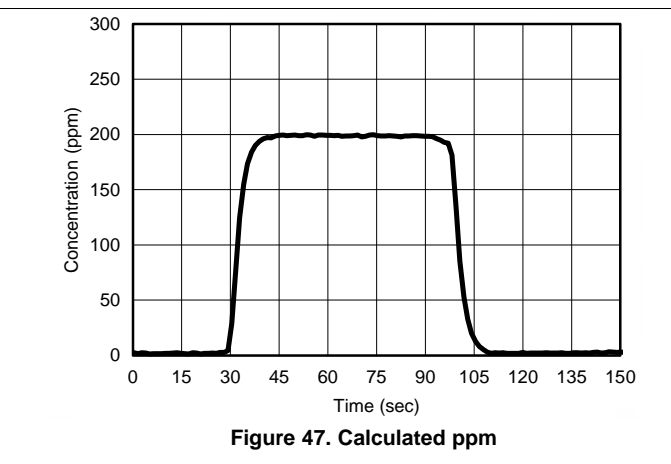


Figure 47. Calculated ppm

Figure 46 shows the calculated sensor current using the formula in Equation 7 :

$$I_{SENSOR} = V_{DIFF} / R_F = 1.52V / 110 \text{ k}\Omega = 13.8\mu A \tag{7}$$

Equation 8 shows the resulting conversion of the sensor current into ppm.

$$\text{ppm} = I_{SENSOR} / I_{PERPPM} = 13.8\mu A / 69nA = 200 \tag{8}$$

Total supply current for the amplifier section is less than 700 nA, minus sensor current. Note that the sensor current is sourced from the amplifier output, which in turn comes from the amplifier supply voltage. Therefore, any continuous sensor current must also be included in supply current budget calculations.

### 8.3 Do's and Don'ts

Do properly bypass the power supplies.

Do add series resistance to the output when driving capacitive loads, particularly cables, Muxes and ADC inputs.

Do add series current limiting resistors and external schottky clamp diodes if input voltage is expected to exceed the supplies. Limit the current to 1mA or less (1K $\Omega$  per volt).

## 9 Power Supply Recommendations

The LPV80x is specified for operation from 1.6 V to 5.5 V ( $\pm 0.8$  V to  $\pm 2.75$  V) over a  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  temperature range. Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the [Typical Characteristics](#).

### CAUTION

Supply voltages larger than 6 V can permanently damage the device.

For proper operation, the power supplies must be properly decoupled. For decoupling the supply lines it is suggested that 100 nF capacitors be placed as close as possible to the operational amplifier power supply pins. For single supply, place a capacitor between  $V^+$  and  $V^-$  supply leads. For dual supplies, place one capacitor between  $V^+$  and ground, and one capacitor between  $V^-$  and ground.

Low bandwidth nanopower devices do not have good high frequency ( $> 1$  kHz) AC PSRR rejection against high-frequency switching supplies and other 1 kHz and above noise sources, so extra supply filtering is recommended if kilohertz or above noise is expected on the power supply lines.

## 10 Layout

### 10.1 Layout Guidelines

The  $V^+$  pin should be bypassed to ground with a low ESR capacitor.

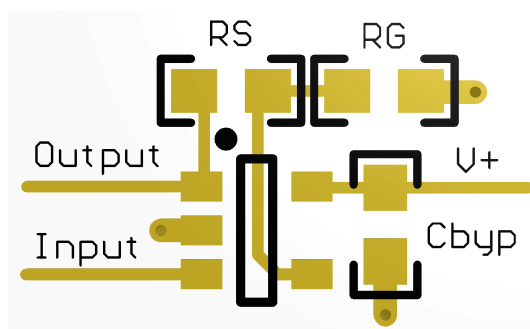
The optimum placement is closest to the  $V^+$  and ground pins.

Care should be taken to minimize the loop area formed by the bypass capacitor connection between  $V^+$  and ground.

The ground pin should be connected to the PCB ground plane at the pin of the device.

The feedback components should be placed as close to the device as possible to minimize strays.

### 10.2 Layout Example



**Figure 48. SOT-23 Layout Example (Top View)**

## 11 Device and Documentation Support

### 11.1 Device Support

#### 11.1.1 Development Support

TINA-TI SPICE-Based Analog Simulation Program, <http://www.ti.com/tool/tina-ti>

DIP Adapter Evaluation Module, <http://www.ti.com/tool/dip-adapter-evm>

TI Universal Operational Amplifier Evaluation Module, <http://www.ti.com/tool/opampevm>

TI FilterPro Filter Design software, <http://www.ti.com/tool/filterpro>

#### 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 11.3 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

**Table 1. Related Links**

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
LPV801	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>
LPV802	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>

#### 11.4 Trademarks

All trademarks are the property of their respective owners.

#### 11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LPV801DBVR	PREVIEW	SOT-23	DBV	5	3000	TBD	Call TI	Call TI	-40 to 125		
LPV801DBVT	PREVIEW	SOT-23	DBV	5	250	TBD	Call TI	Call TI	-40 to 125		
LPV802DGKR	PREVIEW	VSSOP	DGK	8	2500	TBD	Call TI	Call TI	-40 to 125		
LPV802DGKT	PREVIEW	VSSOP	DGK	8	250	TBD	Call TI	Call TI	-40 to 125		
PLPV801DBVT	PREVIEW	SOT-23	DBV	5	250	TBD	Call TI	Call TI	-40 to 125		

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

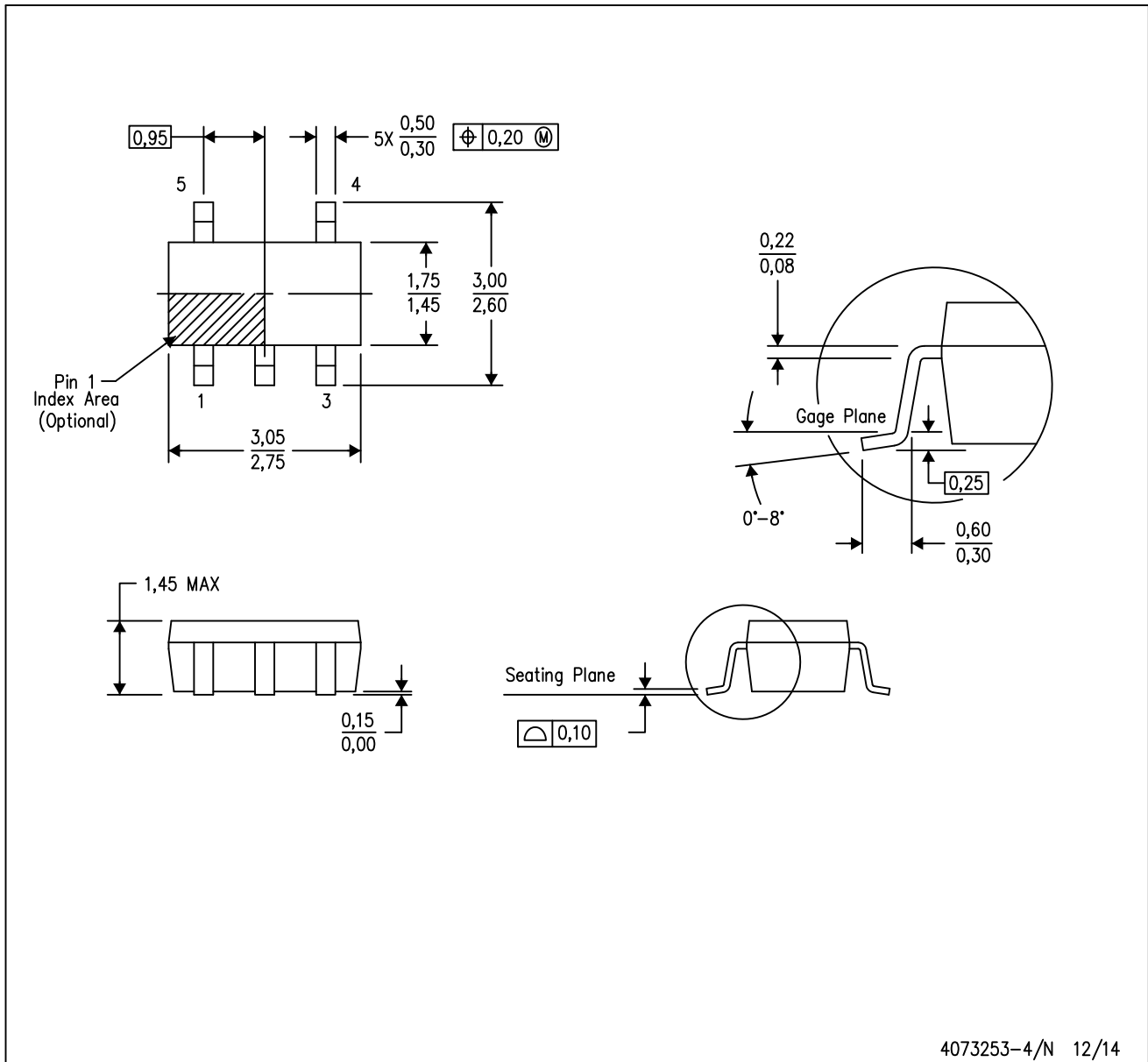
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DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
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  - This drawing is subject to change without notice.
  - Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - Falls within JEDEC MO-178 Variation AA.



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DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>
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Power Mgmt	<a href="http://power.ti.com">power.ti.com</a>
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Energy and Lighting	<a href="http://www.ti.com/energy">www.ti.com/energy</a>
Industrial	<a href="http://www.ti.com/industrial">www.ti.com/industrial</a>
Medical	<a href="http://www.ti.com/medical">www.ti.com/medical</a>
Security	<a href="http://www.ti.com/security">www.ti.com/security</a>
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